# **Small Signal MOSFET**

# 20 V, 220 mA, Dual N–Channel, 1.0 mm x 1.0 mm SOT–963 Package

### Features

- Dual N-Channel MOSFET
- Offers a Low  $R_{DS(ON)}$  Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- This is a Pb–Free Device

### Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment
- Analog Switch

### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

Para	Parameter				Unit		
Drain-to-Source Voltag	Drain-to-Source Voltage				V		
Gate-to-Source Voltag	V <sub>GS</sub>	±8	V				
Continuous Drain	Steady	$T_A = 25^{\circ}C$		220			
Current (Note 1)	State	$T_A = 85^{\circ}C$	ID	160	mA		
	$t \le 5 s$	$T_A = 25^{\circ}C$		280			
Power Dissipation	Steady State T <sub>A</sub> = 25°C			125	mW		
(Note 1)			PD				
	t ≤ 5 s			200			
Pulsed Drain Current		t <sub>p</sub> = 10 μs	I <sub>DM</sub> 800		mA		
Operating Junction and	Storage Tem	perature	_T <sub>J</sub> ,	–55 to	°C		
		T <sub>STG</sub>	150				
Source Current (Body I	IS	200	mA				
Lead Temperature for S (1/8" from case for 1		oses	Τ <sub>L</sub>	260	°C		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

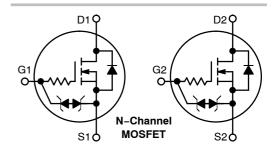
2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

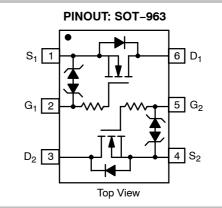


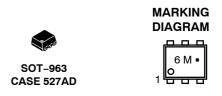
## **ON Semiconductor®**

#### http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> Max
20 V -	1.5 Ω @ 4.5 V	
	2.0 Ω @ 2.5 V	0.22 A
	3.0 Ω @ 1.8 V	0.22 A
	4.5 Ω @ 1.5 V	







<sup>=</sup> Specific Device Code

= Date Code

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Μ

= Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient – Steady State (Note 3)	<b>D</b> a ta	1000	°C/W
Junction-to-Ambient – t = 5 s (Note 3)	$R_{\theta JA}$	600	0/11

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS		•					
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D = 2$	250 μA	20			V
Zero Gate Voltage Drain Current			$T_J = 25^{\circ}C$			50	nA
	I <sub>DSS</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 5 V	$T_J = 85^{\circ}C$			200	- 1
		$V_{GS}$ = 0 V, $V_{DS}$ = 16 V	T <sub>J</sub> = 25°C			100	nA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ =	±5.0 V			±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 1$	00 μΑ	0.52		1.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>					2.0	mV/°C
Drain-to-Source On Resistance		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> =	100 mA		0.75	1.5	
		$V_{GS}$ = 2.5 V, I <sub>D</sub> =	50 mA		1.0	2.0	
	R <sub>DS(ON)</sub>	$V_{GS}$ = 1.8 V, I <sub>D</sub> = 20 mA $V_{GS}$ = 1.5 V, I <sub>D</sub> = 10 mA			1.4	3.0	Ω
					1.8	4.5	
		V <sub>GS</sub> = 1.2 V, I <sub>D</sub> =	1.0 mA		2.8		

## CAPACITANCES

Forward Transconductance

Source-Drain Diode Voltage

Input Capacitance	C <sub>ISS</sub>		12.5	
Output Capacitance	C <sub>OSS</sub>	f = 1.0 MHz, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 15 V	3.6	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	20	2.6	

**g**fs

 $V_{SD}$ 

 $V_{DS} = 5.0 \text{ V}, I_D = 125 \text{ mA}$ 

 $V_{GS}$  = 0 V,  $I_S$  = 10 mA

0.48

0.6

1.0

S

V

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 4.5 V (Note 4)

Turn-On Delay Time	t <sub>d(ON)</sub>		16.5	
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DD</sub> = 10 V, I <sub>D</sub> = 200 mA,	25.5	20
Turn-Off Delay Time	t <sub>d(OFF)</sub>	R <sub>G</sub> = 2.0 Ω	142	ns
Fall Time	t <sub>f</sub>		80	

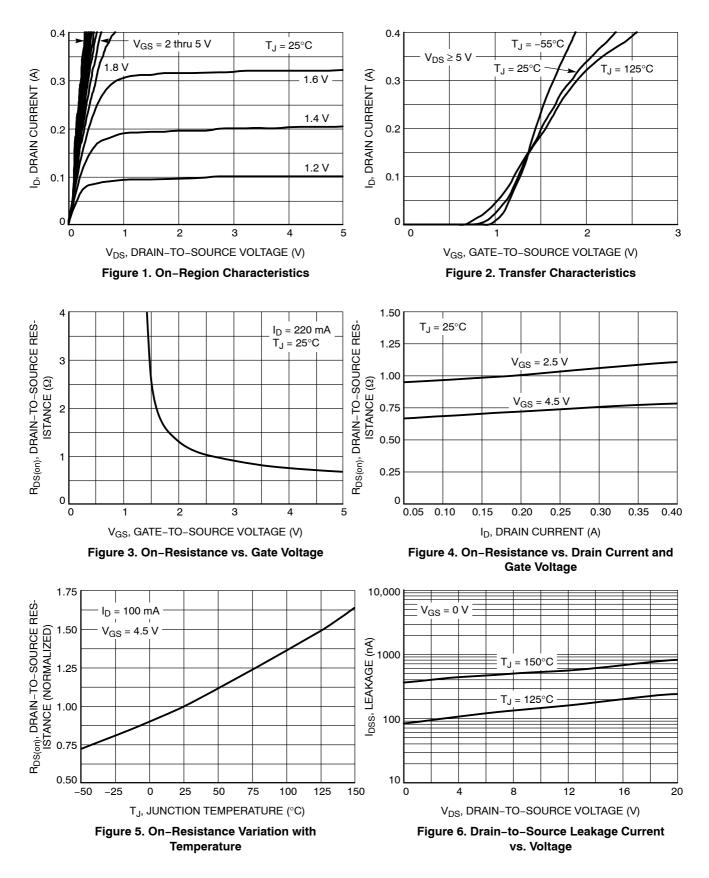
4. Switching characteristics are independent of operating junction temperatures.

#### **ORDERING INFORMATION**

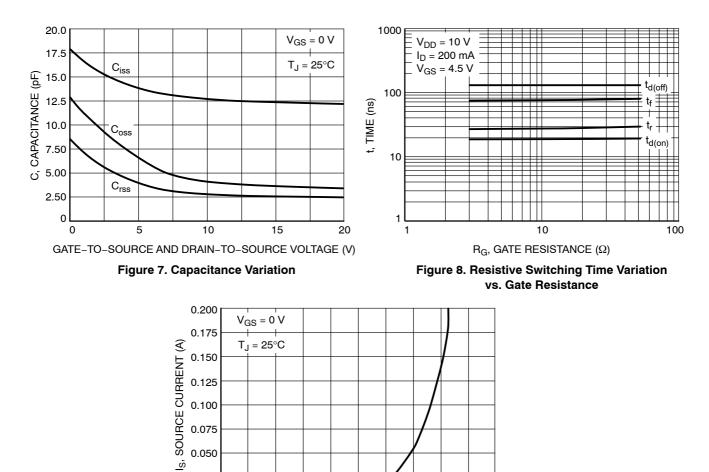
Device	Package	Shipping <sup>†</sup>
NTUD3174NZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **TYPICAL CHARACTERISTICS**



## **TYPICAL CHARACTERISTICS**



0.025

0.2

0.4

V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

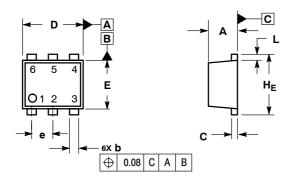
0.6

0.8

1

#### PACKAGE DIMENSIONS

SOT-963 CASE 527AD ISSUE D



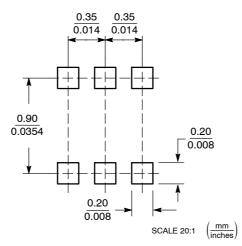
NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS

2

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS				INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.34	0.37	0.40					
b	0.10	0.15	0.20	0.004	0.006	0.008		
С	0.07	0.12	0.17	0.003	0.005	0.007		
D	0.95	1.00	1.05	0.037	0.039	0.041		
Е	0.75	0.80	0.85	0.03	0.032	0.034		
е		0.35 BSC			0.014 BSC			
L	0.05	0.10	0.15	0.002	0.004	0.006		
HE	0.95	1.00	1.05	0.037	0.039	0.041		

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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